

FIGURE 1

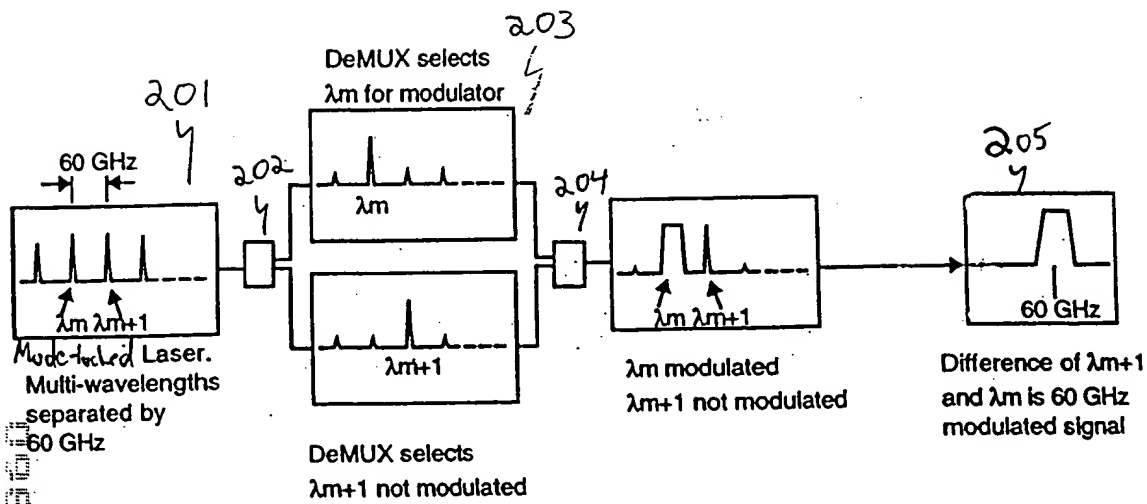
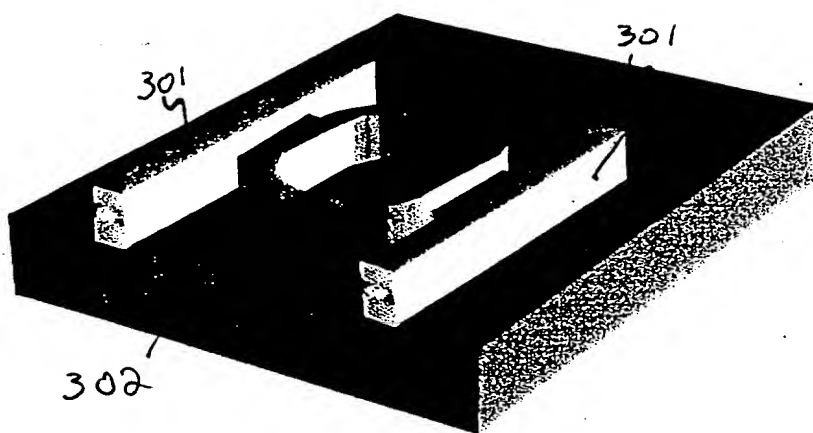
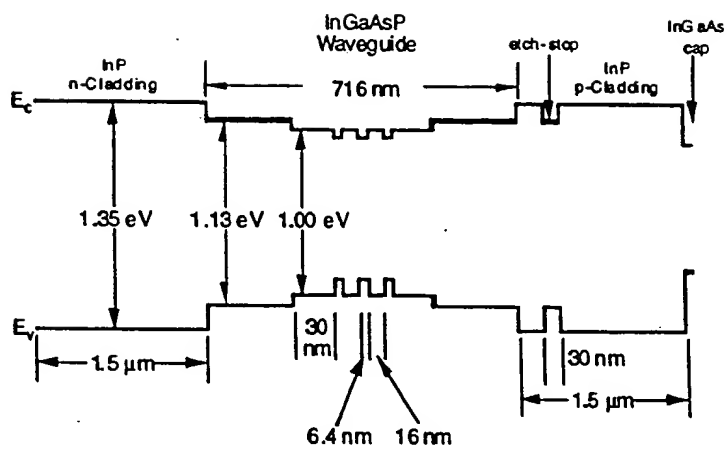


FIGURE 2



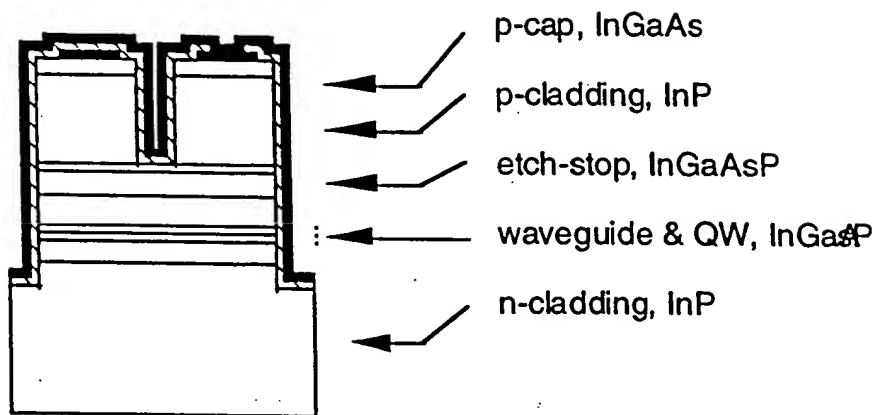
Schematic drawing of the racetrack laser.

FIGURE 3



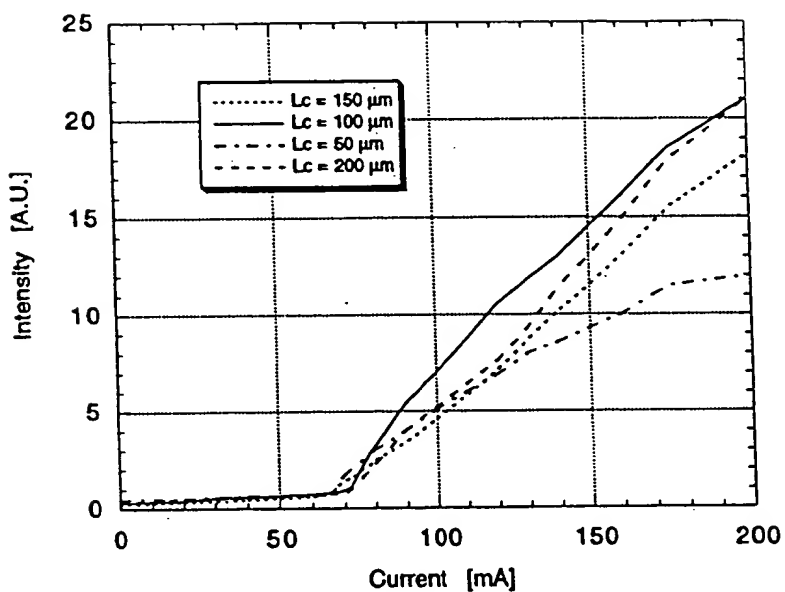
The schematic drawing of the epitaxial structure.

FIGURE 4



A schematic diagram of the wafer view shown in cross section taken from the coupling region between the ring and the straight sections.

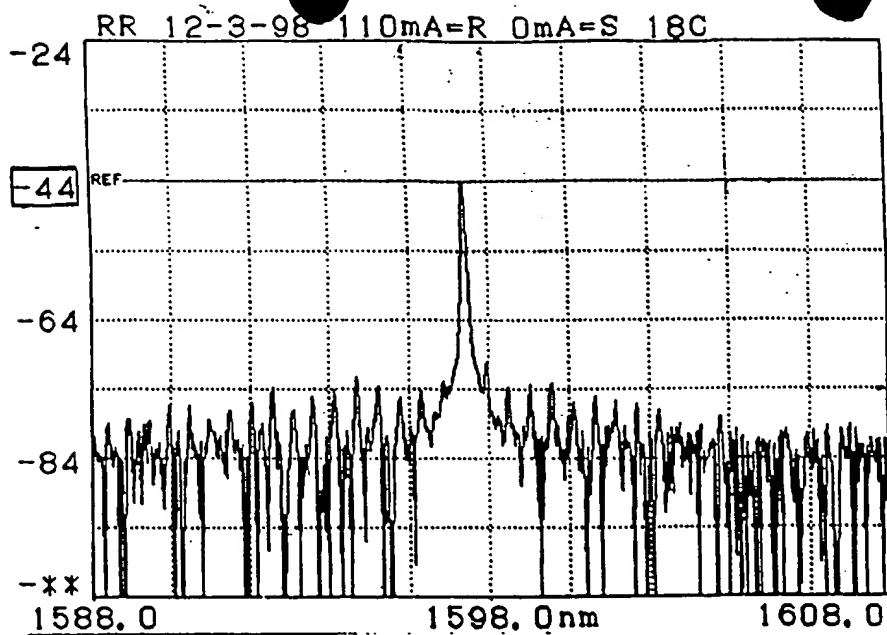
FIGURE 5



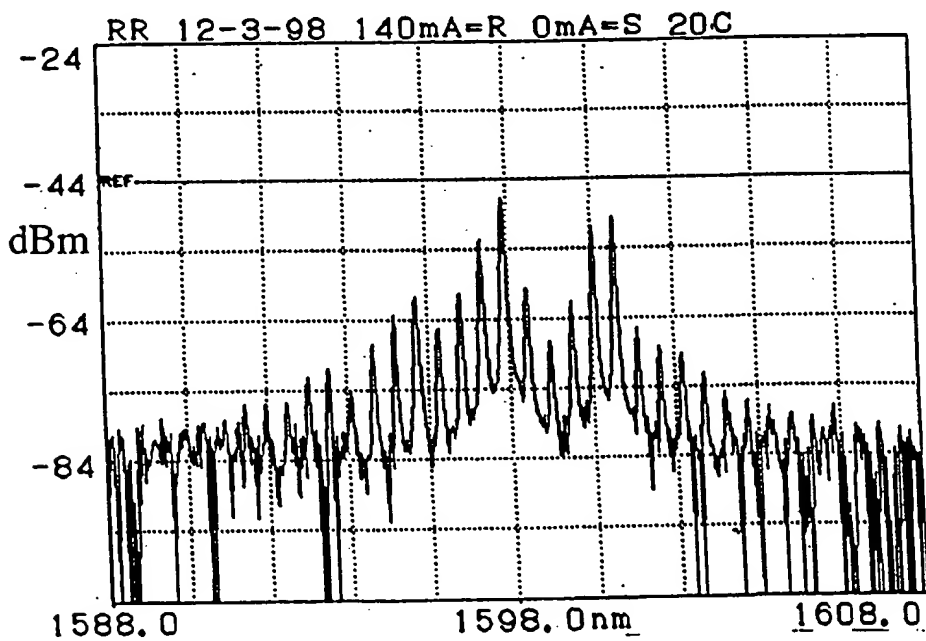
L-I curve for the racetrack laser with a coupling length ranging from 50-200μm showing nearly the same threshold current for all configurations, but with improved differential efficiency for the 100μm coupler.

FIGURE 6

FIGURE 7

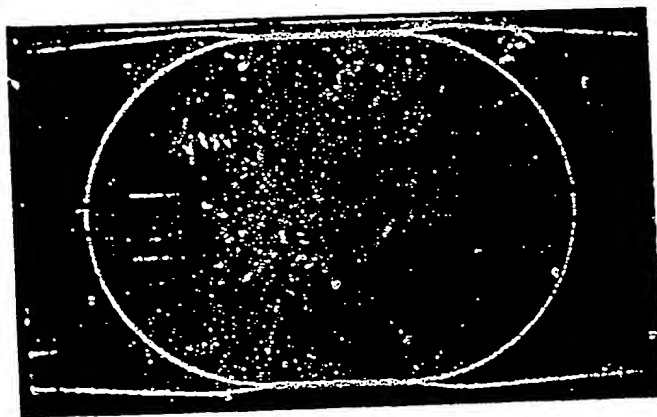


Lasing spectrum of the racetrack laser at a drive current $I = 110$ mA, showing single mode operation with an SMSR = 26 dB. Single-mode operation is maintained from threshold to nearly $2 I_{th}$.



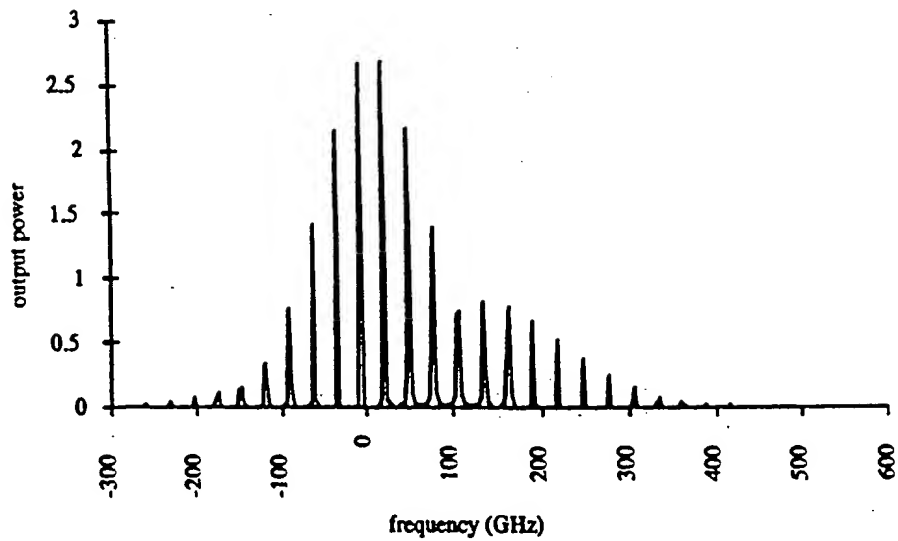
Lasing spectrum at a drive current $I = 140$ mA. An abrupt transition from single-mode (see Fig. 7) to multi-mode operation, apparently due to self-pulsating.

FIGURE 8



Dual-absorber mode-locked racetrack laser fabricated in GaAlAs/GaAs.

FIGURE 9



Computed output spectrum of a passively mode-locked racetrack laser.

FIGURE 10